



All Purpose InGaAs p-i-n Photodiode

35PD300LDC-S

The 35PD300LDC-S, an InGaAs photodiode with a 300 μ m-diameter photosensitive region and mounted on a metallized ceramic substrate, is a low-dark-current version of the 35PD300-S, one of Telcom Devices' most versatile detectors. Applications include high sensitivity instrumentation, laser back-facet monitoring, and moderate-bit-rate telecomm and datacomm transmission. Planar semiconductor design and dielectric passivation provide for superior noise performance. Reliability is assured by a 100% purge burn-in (200°C, 15 hours, $V_r = 15V$). Chips can also be attached and wire bonded to customer-supplied or other specified submounts.

Features

Planar Structure
Dielectric Passivation
100% Purge Burn-In
High Responsivity

Device Characteristics						
Parameters	Test Conditions	Min	Typ	Max	Units	
Operating Voltage	-	-	-	-15	Volts	
Dark Current	-5V	-	-	0.51	nA	
Capacitance	-5V	-	4	12	pF	
Responsivity	1300nm	0.70	0.9	-	A/W	
	1500nm	-	1.0	-	A/W	
Rise/Fall	-	-	-	3	ns	
Absolute Maximum Ratings						
Reverse Voltage						20 Volts
Forward Current						25 mA
Reverse Current						5 mA
Operating Temperature						-40°C to + 85°C
Storage Temperature						-40°C to + 85°C
Soldering Temperature						250°C